UNISONIC TECHNOLOGIES CO., LTD

5N60K-TCQ **Preliminary Power MOSFET**

5A, 600V N-CHANNEL **POWER MOSFET**

DESCRIPTION

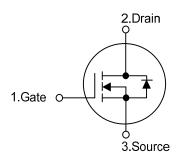
The UTC 5N60K-TCQ is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)}$ < 2.5 Ω @ V_{GS} =10V, I_{D} = 2.5A
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

TO-220 TO-220F1 TO-252

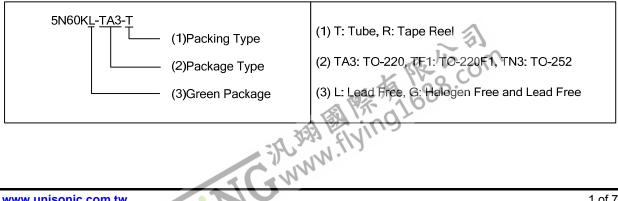
SYMBOL



ORDERING INFORMATION

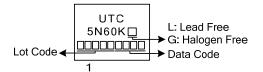
Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
5N60KL-TA3-T	5N60KG-TA3-T	TO-220	G	D	S	Tube	
5N60KL-TF1-T	5N60KG-TF1-T	TO-220F1	G	D	S	Tube	
5N60KL-TN3-R	5N60KG-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



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MARKING





■ **ABSOLUTE MAXIMUM RATINGS** (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V _{DSS}	600	V	
Gate-Source Voltage		V_{GSS}	±30	V	
Drain Current	Continuous	I _D	5.0	Α	
	Pulsed (Note 2)	I _{DM}	20	Α	
Avalanche Current (Note 2)		I _{AR}	4.0	Α	
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	80	mJ	
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.25	V/ns	
Power Dissipation	TO-220		106	W	
	TO-220F1	P _D	36	W	
	TO-252		50	W	
Junction Temperature		TJ	+150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. L = 10mH, I_{AS} = 4.0A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C
- 4. $I_{SD} \le 5.0 \text{A}$, di/dt $\le 200 \text{A}/\mu \text{s}$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ} \text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220F/TO-220F1	0	62.5	°C/W
	TO-252	$ heta_{JA}$	110	°C/W
Junction to Case	TO-220		1.18	°C/W
	TO-220F1	θ_{JC}	3.47	°C/W
	TO-252		2.5	°C/W



ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

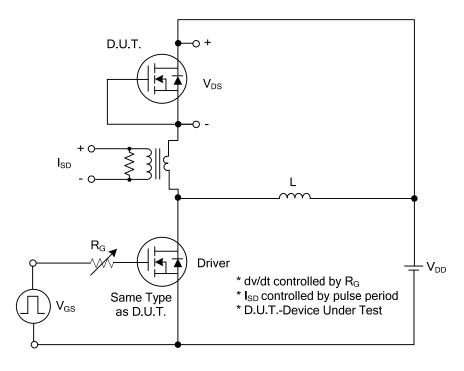
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	600			V	
Drain-Source Leakage Current		I _{DSS}	V _{DS} =600V, V _{GS} =0V			1	μA	
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =30V, V _{DS} =0V			100	^	
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	2.0		4.0	V	
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =2.5A			2.5	Ω	
DYNAMIC CHARACTERISTICS	_							
Input Capacitance		C_{ISS}			480		pF	
Output Capacitance		Coss	V_{GS} =0V, V $_{DS}$ =25V, f=1.0MHz		60		pF	
Reverse Transfer Capacitance		C_{RSS}			6.5		pF	
SWITCHING CHARACTERISTICS								
Total Gate Charge (Note 1)		Q_{G}	V -50V I -1 3A V -10V		46		nC	
Gate to Source Charge		Q_GS	V _{DS} =50V, I _D =1.3A, V _{GS} =10V -I _G =100μA (Note 1, 2)		4.6		nC	
Gate to Drain Charge		Q_GD	IG-100μΑ (Note 1, 2)		6.0		nC	
Turn-ON Delay Time (Note 1)		$t_{D(ON)}$			42		ns	
Rise Time		t_R	V_{DD} =30V, V_{GS} =10V, I_{D} =0.5A,		44		ns	
Turn-OFF Delay Time		$t_{D(OFF)}$	R _G =25Ω (Note 1, 2)		120		ns	
Fall-Time	-				38		ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Continuous	Current	Is				5	Α	
Maximum Body-Diode Pulsed Current		I _{SM}				20	Α	
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I _S =5.0A, V _{GS} =0V			1.4	V	
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	I _S =5.0A, V _{GS} =0V,		390		nS	
Body Diode Reverse Recovery Charge		Q_{rr}	dI _F /dt=100A/μs		1.6		μC	

Note: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle ≤ 2%

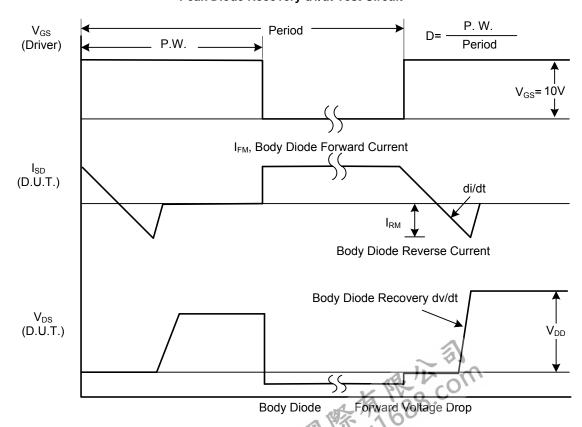


^{2.} Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

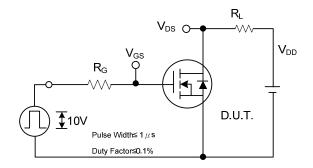


Peak Diode Recovery dv/dt Test Circuit

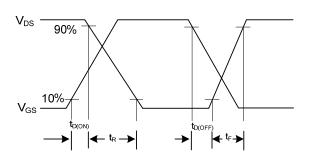


Peak Diode Recovery dv/dt Waveforms

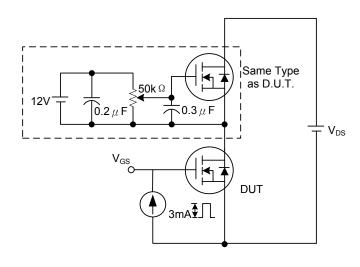
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



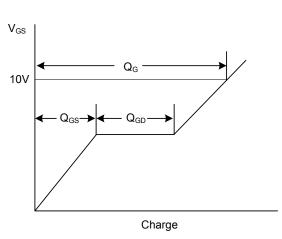
Switching Test Circuit



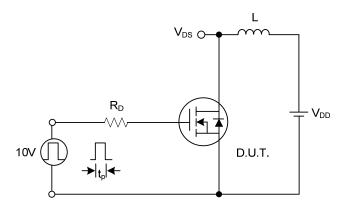
Switching Waveforms



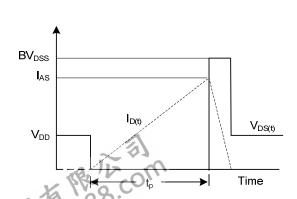
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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